

REMARKS

Reconsideration of this application is respectfully requested. Claim 1 has been amended to remove restrictions to cleaning gasses and to positively recite various fluid couplings and physical orientations of elements of the chemical vapor deposition system. Support for these amendments may be found in the specification as filed, for example at paragraphs 21-23, 26 and 27. No new matter is added.

Claim 1 is patentable over van Os, US 5,792,272, which the office action concedes fails to teach a first gas source. Office Action at p.9.

Claim 1 is further patentable over van Os in view of Muruges, US 6,450,117, which is cited for describing a gas source. Even if such a gas source were present in the system described by van Os, however, van Os would still not teach all of the features presently recited in claim 1. For example, the system described in van Os does not include a lid supporting a shower head disposed within the chemical vapor deposition chamber and separate from the first gas distribution channel, wherein that lid has an interior rim including a plurality of cleaning gas injection ports each of which is fluidly connected to a gas distribution channel, and various ones of which are oriented at different angles with respect to an interior of a wall of the chemical vapor deposition chamber, said wall being attached to said lid, as presently claimed.

If there are any additional fees due in connection with this communication, please charge Deposit Account No. 19-3140.

Respectfully submitted,
SONNENSCHN NATH & ROSENTHAL LLP

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/s/Tarek N. Fahmi/
Tarek N. Fahmi
Reg. No. 41,402

P.O. Box 061080
Wacker Drive Station
Sears Tower
Chicago, IL 60606-1080
(415) 882-5023